

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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# 2SB1409(L)/(S)

Silicon PNP Epitaxial

**RENESAS**

ADE-208-877 (Z)

1st. Edition

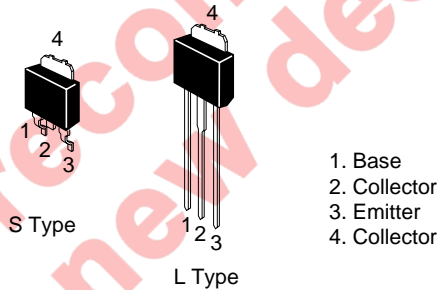
September 2000

## Application

Low frequency power amplifier complementary Pair with 2SD2123(L)/(S)

## Outline

DPAK



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	−180	V
Collector to emitter voltage	V <sub>CEO</sub>	−160	V
Emitter to base voltage	V <sub>EBO</sub>	−5	V
Collector current	I <sub>C</sub>	−1.5	A
Collector peak current	I <sub>C(peak)</sub>	−3	A
Collector power dissipation	P <sub>C</sub> <sup>*1</sup>	18	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	−55 to +150	°C

Note: 1. Value at T<sub>C</sub> = 25°C.

Electrical Characteristics (Ta = 25°C)

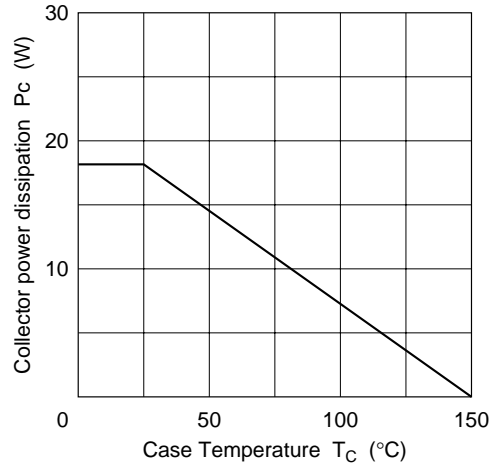
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	−180	—	—	V	I <sub>C</sub> = −1 mA, I <sub>E</sub> = 0
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	−160	—	—	V	I <sub>C</sub> = −10 mA, R <sub>BE</sub> = ∞
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	−5	—	—	V	I <sub>E</sub> = −1 mA, I <sub>C</sub> = 0
Collector cutoff current	I <sub>CBO</sub>	—	—	−10	μA	V <sub>CB</sub> = −160 V, I <sub>E</sub> = 0
DC current transfer ratio	h <sub>FE1</sub> <sup>*1</sup>	60	—	200		V <sub>CE</sub> = −5 V, I <sub>C</sub> = −150 mA <sup>*2</sup>
	h <sub>FE2</sub>	30	—	—		V <sub>CE</sub> = −5 V, I <sub>C</sub> = −500 mA <sup>*2</sup>
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	—	—	−1	V	I <sub>C</sub> = −500 mA, I <sub>B</sub> = −50 mA
Base to emitter voltage	V <sub>BE</sub>	—	—	−1.5	V	V <sub>CE</sub> = −5 V, I <sub>C</sub> = −150 mA
Gain bandwidth product	f <sub>T</sub>	—	240	—	MHz	V <sub>CE</sub> = −5 V, I <sub>C</sub> = −150 mA
Collector output capacitance	C <sub>ob</sub>	—	25	—	pF	V <sub>CB</sub> = −10 A, I <sub>E</sub> = 0, f = 1 MHz

Notes: 1. The 2SB1409(L)/(S) is grouped by h<sub>FE1</sub> as follows.

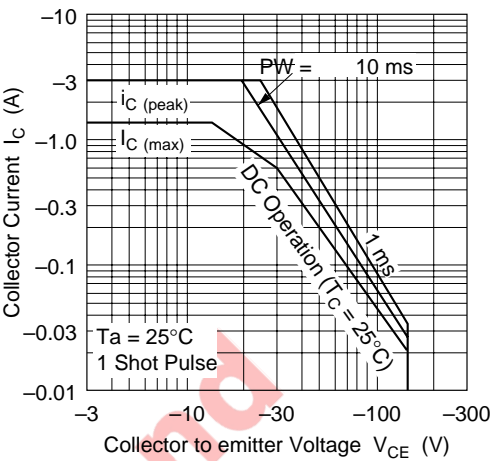
B	C
60 to 120	100 to 200

2. Pulse test.

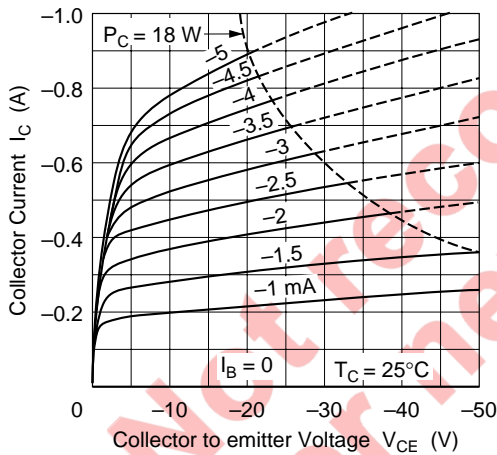
Maximum Collector Dissipation Curve



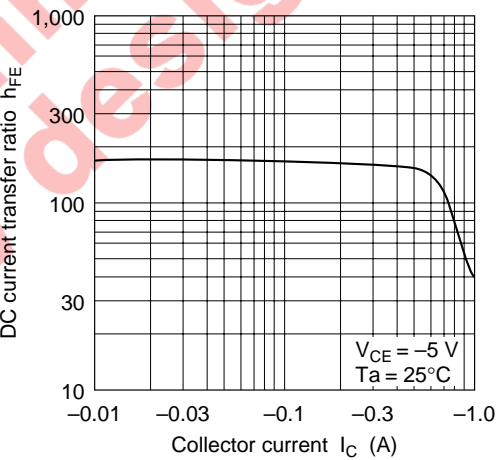
Area of Safe Operation

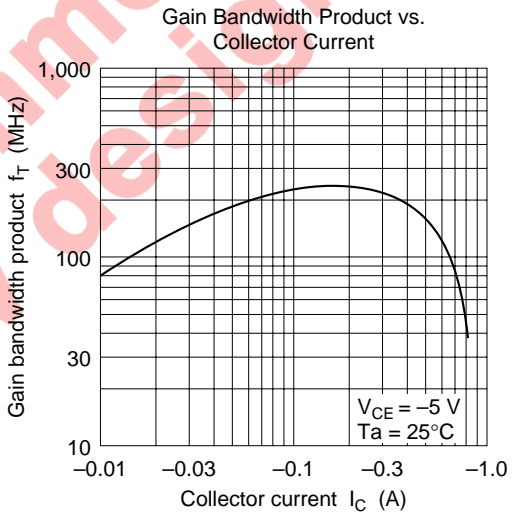
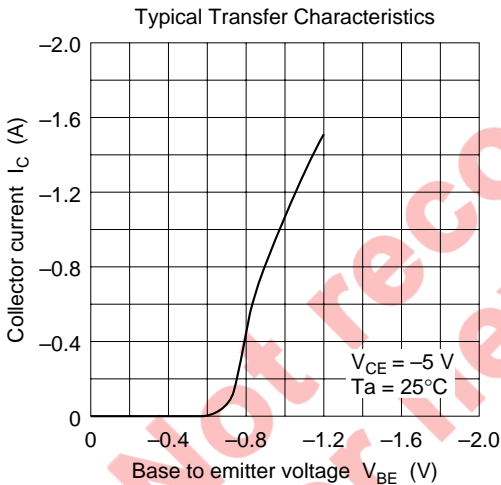
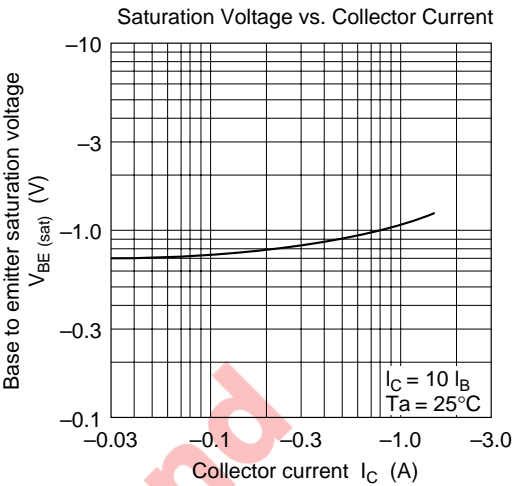
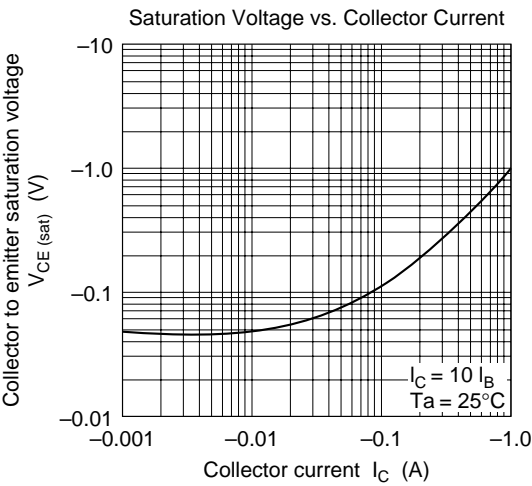


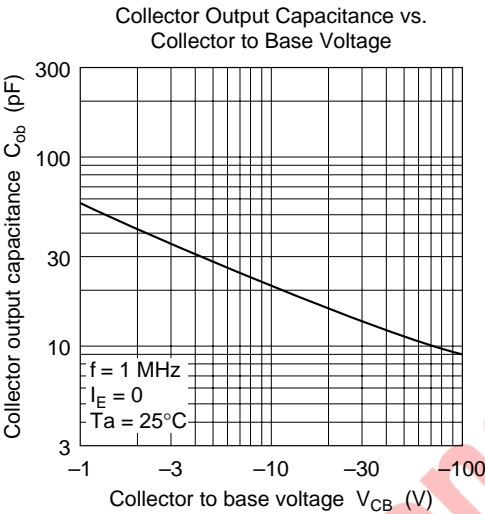
Typical Output Characteristics



DC Current Transfer Ratio vs. Collector Current







Not recommended  
for new design

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# HITACHI

## **Hitachi, Ltd.**

Semiconductor & IC Div.  
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan  
Tel: Tokyo (03) 3270-2111  
Fax: (03) 3270-5109

### **For further information write to:**

Hitachi America, Ltd.  
Semiconductor & IC Div.  
2000 Sierra Point Parkway  
Brisbane, CA. 94005-1835  
U S A  
Tel: 415-589-8300  
Fax: 415-583-4207

Hitachi Europe GmbH  
Electronic Components Group  
Continental Europe  
Domacher Straße 3  
D-85622 Feldkirchen  
München  
Tel: 089-9 91 80-0  
Fax: 089-9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Div.  
Northern Europe Headquarters  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA  
United Kingdom  
Tel: 0628-585000  
Fax: 0628-778322

Hitachi Asia Pte. Ltd.  
16 Collyer Quay #20-00  
Hitachi Tower  
Singapore 0104  
Tel: 535-2100  
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.  
Unit 706, North Tower,  
World Finance Centre,  
Harbour City, Canton Road  
Tsim Sha Tsui, Kowloon  
Hong Kong  
Tel: 27359218  
Fax: 27306071